NPN general purpose transistor **SSTA28 / MMSTA28**

Features

1) BVces < 80V (Ic=100µA)

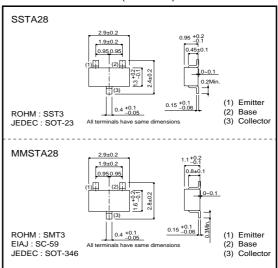
Package, marking and packaging specifications

	-	-
Part No.	SSTA28	MMSTA28
Packaging type	SST3	SMT3
Marking	RAT	RAT
Code	T116	T146
Basic ordering unit (pieces)	3000	3000

•Absolute maximum ratings (Ta=25°C)

	-		
Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	80	V
Collector-emitter voltage	VCEO	80	V
Emitter-base voltage	Vebo	12	V
Collector current	lc	0.3	A
Collector power dissipation	Pc	0.2	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

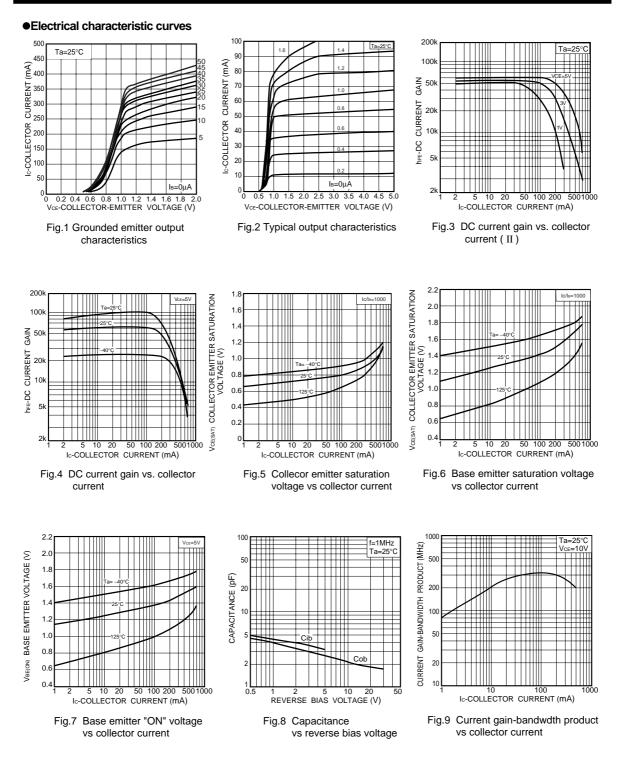
•External dimensions (Unit : mm)



Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	80	-	-	V	Ic = 100μA
Collector-emitter breakdown voltage	BVCES	80	-	-	V	Ic = 100μA
Emitter-base breakdown voltage	ВУево	12	-	-	V	Ιε = 10μΑ
Collector cutoff current	Ісво	-	-	0.1	μΑ	Vcb = 60V
	Івео	-	-	0.1	μΑ	VEB = 10V
	ICES	-	_	0.5	μΑ	Vce = 10V
Collector-emitter saturation voltage	VCE(sat) 1	-	0.7	1.2	V	Ic/I _B = 10mA/10μA
	VCE(sat) 2	-	0.8	1.5	V	Ic/Iв = 100mA/0.1mA
Base-emitter saturation voltage	VBE(on)	-	1.4	2.0	V	Vce/IB = 5V/100mA
DC current transfer ratio	hfe	10000	_	-	-	Vce = 5V , Ic = 10mA
		10000	_	-		Vce = 5V , Ic = 100mA
Transition frequency	f⊤	125	200	-	MHz	Vce = 5V , Ie = 10mA , f = 100MHz
Output Capecitance	Cob	-	5.0	8.0	pF	$V_{CB} = 10V$, $I_E = 0$, $f = 1MHz$

Transistors



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